

BAS19L, BAS20L, BAS21L, BAS21DW5

High Voltage Switching Diode

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	120 200 250	Vdc
Repetitive Peak Reverse Voltage	V_{RRM}	120 200 250	Vdc
Continuous Forward Current	I_F	200	mAdc
Peak Forward Surge Current (1/2 Cycle, Sine Wave, 60 Hz)	I_{FSM}	2	A
Repetitive Peak Forward Current (Pulse Train: $T_{ON} = 1$ s, $T_{OFF} = 0.5$ s)	I_{FRM}	0.6	A
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Power Dissipation (Note 1)	P_D	385	mW
Electrostatic Discharge	ESD	HM < 500 MM < 400	V V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

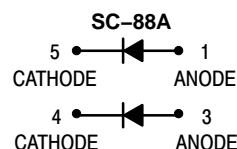
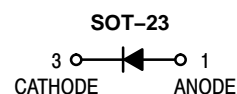
1. Mounted on FR-5 Board = 1.0 x 0.75 x 0.062 in.



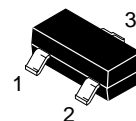
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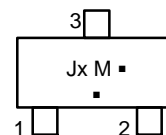
HIGH VOLTAGE SWITCHING DIODE



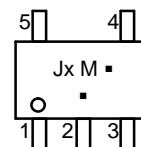
MARKING DIAGRAMS



SOT-23 (TO-236)
CASE 318
STYLE 8



SC-88A (SOT-353)
CASE 419A



x = P, R, or S
P = BAS19L
R = BAS20L
S = BAS21L or BAS21DW5
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon the manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

BAS19L, BAS20L, BAS21L, BAS21DW5

Thermal Characteristics (SOT-23)

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (SOT-23)	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (Note 3) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics (SC-88A)

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P_D	385	mW
Thermal Resistance – Junction-to-Ambient Derate Above 25°C	$R_{\theta JA}$	328	$^\circ\text{C/W}$
		3.0	mW/ $^\circ\text{C}$
Maximum Junction Temperature	T_{Jmax}	150	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

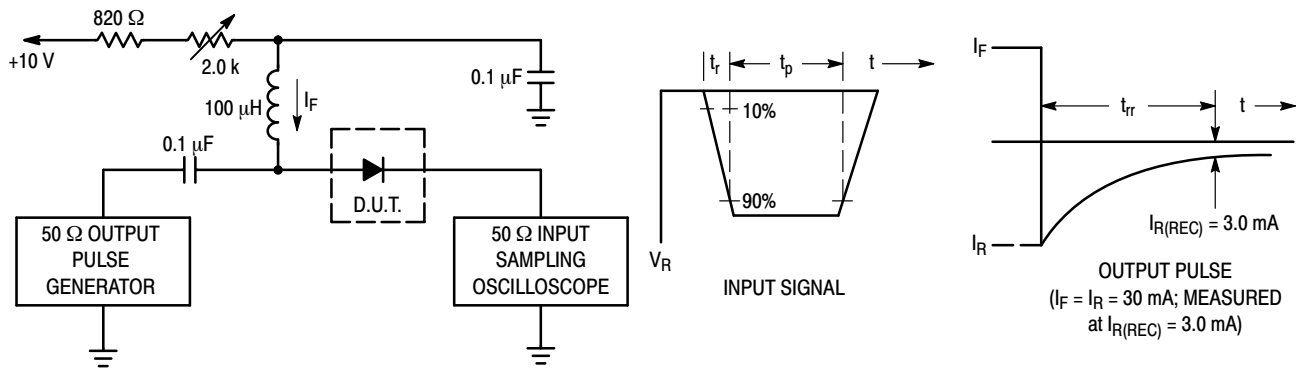
2. FR-5 = 1.0 × 0.75 × 0.062 in.
3. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.
4. Mounted on FR-5 Board = 1.0 × 0.75 × 0.062 in.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current ($V_R = 100\text{ Vdc}$) ($V_R = 150\text{ Vdc}$) ($V_R = 200\text{ Vdc}$) ($V_R = 100\text{ Vdc}, T_J = 150^\circ\text{C}$) ($V_R = 150\text{ Vdc}, T_J = 150^\circ\text{C}$) ($V_R = 200\text{ Vdc}, T_J = 150^\circ\text{C}$)	I_R	-	0.1	μAdc
			BAS19	0.1
			BAS20	0.1
			BAS21	100
			BAS19	100
			BAS20	100
Reverse Breakdown Voltage ($I_{BR} = 100\ \mu\text{Adc}$) ($I_{BR} = 100\ \mu\text{Adc}$) ($I_{BR} = 100\ \mu\text{Adc}$)	$V_{(BR)}$	-	120	Vdc
			BAS19	200
			BAS20	250
Forward Voltage ($I_F = 100\text{ mAdc}$) ($I_F = 200\text{ mAdc}$)	V_F	-	1.0	Vdc
			1.25	
Diode Capacitance ($V_R = 0, f = 1.0\text{ MHz}$)	C_D	-	5.0	pF
Reverse Recovery Time ($I_F = I_R = 30\text{ mAdc}, I_{R(REC)} = 3.0\text{ mAdc}, R_L = 100$)	t_{rr}	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BAS19L, BAS20L, BAS21L, BAS21DW5



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 30 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

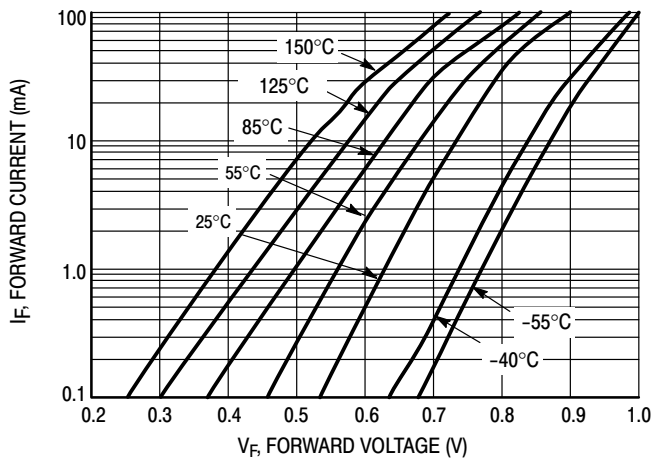


Figure 2. V_F vs. I_F

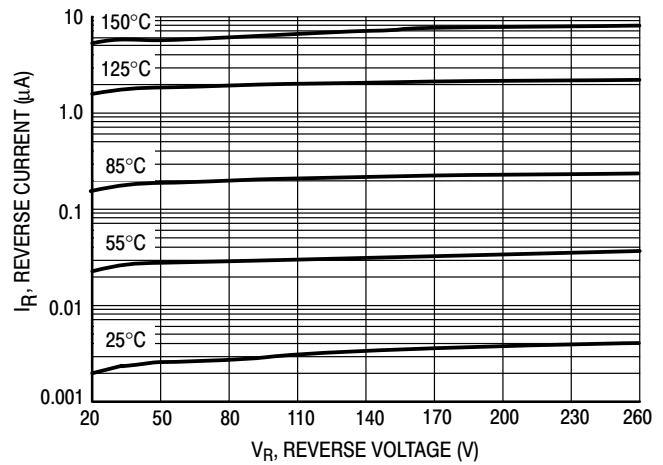


Figure 3. I_R vs. V_R

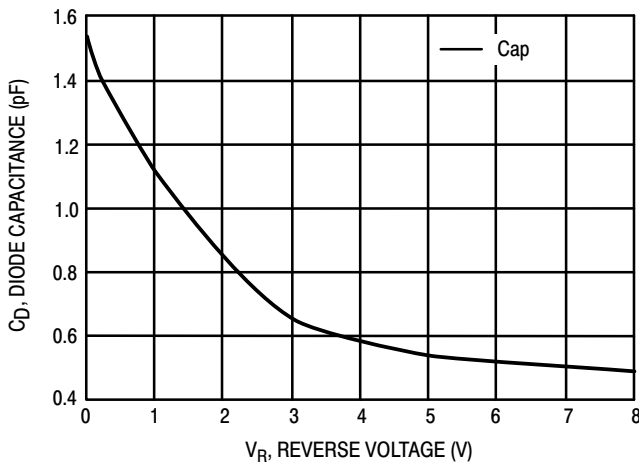


Figure 4. Capacitance

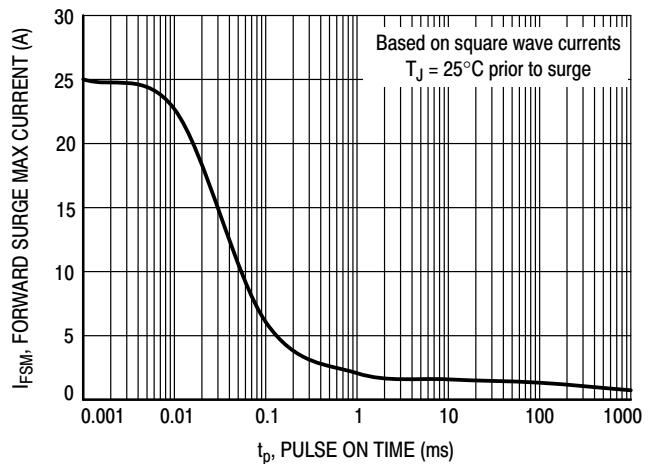


Figure 5. Forward Surge Current

BAS19L, BAS20L, BAS21L, BAS21DW5

ORDERING INFORMATION

Device	Package	Shipping†
BAS19LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS19LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
NSVBAS19LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS20LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS20LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
NSVBAS20LT3G*	SOT-23 (Pb-Free)	10000 / Tape & Reel
SBAS20LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS21LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SBAS21LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS21LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
SBAS21LT3G*	SOT-23 (Pb-Free)	10000 / Tape & Reel
BAS21DW5T1G	SC-88A (Pb-Free)	3000 / Tape & Reel
SBAS21DW5T1G*	SC-88A (Pb-Free)	3000 / Tape & Reel
SBAS21DW5T3G*	SC-88A (Pb-Free)	10000 / Tape & Reel

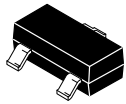
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

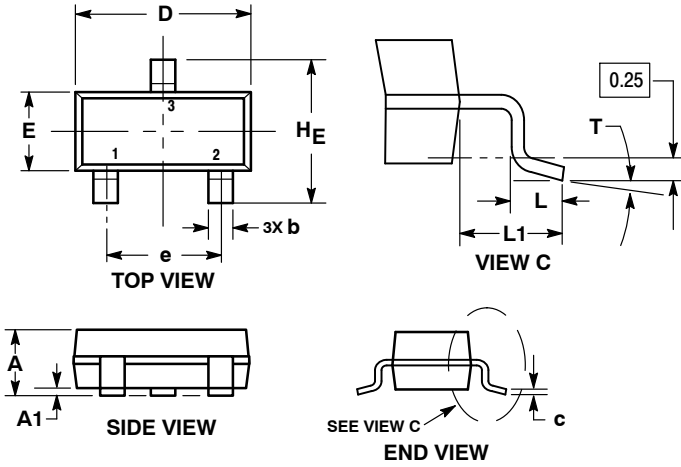
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SOT-23 (TO-236)
CASE 318-08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

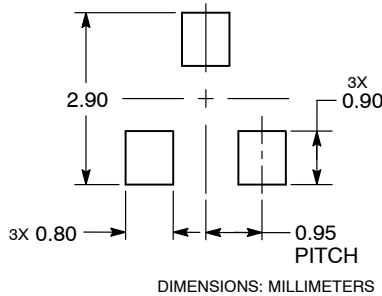


NOTES:

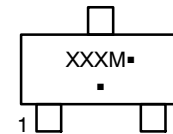
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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DESCRIPTION:	SOT-23 (TO-236)	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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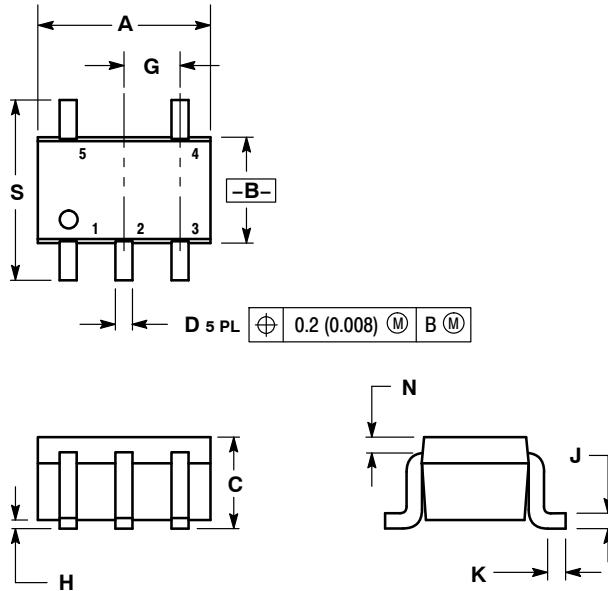
SC-88A (SC-70-5/SOT-353)

CASE 419A-02

ISSUE L

SCALE 2:1

DATE 17 JAN 2013

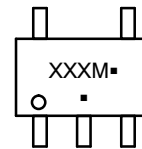


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

GENERIC MARKING DIAGRAM*

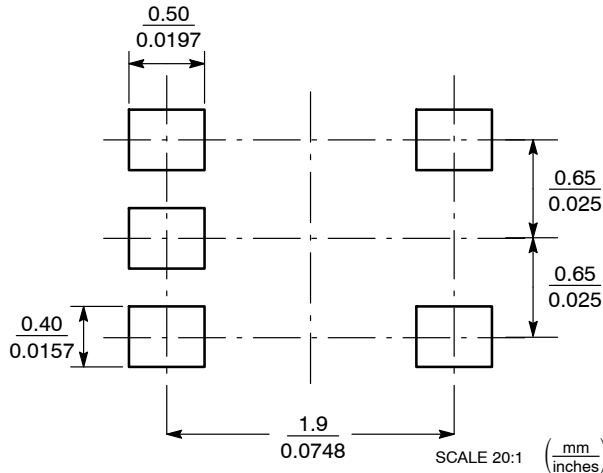


- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking.

SOLDER FOOTPRINT



- STYLE 1:
 PIN 1. BASE
 2. EMITTER
 3. BASE
 4. COLLECTOR
 5. COLLECTOR

- STYLE 2:
 PIN 1. ANODE
 2. EMITTER
 3. BASE
 4. COLLECTOR
 5. CATHODE

- STYLE 3:
 PIN 1. ANODE 1
 2. N/C
 3. ANODE 2
 4. CATHODE 2
 5. CATHODE 1

- STYLE 4:
 PIN 1. SOURCE 1
 2. DRAIN 1/2
 3. SOURCE 1
 4. GATE 1
 5. GATE 2

- STYLE 5:
 PIN 1. CATHODE
 2. COMMON ANODE
 3. CATHODE 2
 4. CATHODE 3
 5. CATHODE 4

- STYLE 6:
 PIN 1. EMITTER 2
 2. BASE 2
 3. EMITTER 1
 4. COLLECTOR
 5. COLLECTOR 2/BASE 1

- STYLE 7:
 PIN 1. BASE
 2. EMITTER
 3. BASE
 4. COLLECTOR
 5. COLLECTOR

- STYLE 8:
 PIN 1. CATHODE
 2. COLLECTOR
 3. N/C
 4. BASE
 5. EMITTER

- STYLE 9:
 PIN 1. ANODE
 2. CATHODE
 3. ANODE
 4. ANODE
 5. ANODE

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